Gaudenzio Meneghesso (IEEE S'95–M'97–SM'07- F'13) He graduated in Electronics Engineering at the University of Padova in 1992 working on the failure mechanism induced by hot-electrons in MESFETs and HEMTs. In 1997 he received the Ph.D. degree in Electrical and Telecommunication Engineering from the University of Padova. Since 2011 is with University of Padova as Full Professor. His research interests involve mainly the Electrical characterization, modeling and reliability of semiconductors devices, in particular power devices based on wide bandgap semiconductors (GaN, SiC, Ga₂O₃). Within these activities he published more than 800 technical papers (of which more than 100 Invited Papers and 15 best paper awards). He has been the principal investigator of an H2020 EU project (InRel-NPower, GA 720527), the local coordinator of several international research project (H2020, ENIAC, ECSEL) and the prime responsible of several research contract with industry and research institute He has been nominated to IEEE Fellow class 2013, with the following citation: "for contributions to the reliability physics of compound semiconductors devices".